

P-Channel 20-V (D-S) MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A) ^d	Q _g (Typ.)
- 20	0.066 at V _{GS} = - 4.5 V	- 3.8	9 nC
	0.086 at V _{GS} = - 2.5 V	- 3.3	

FEATURES

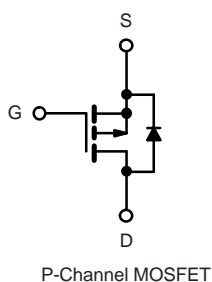
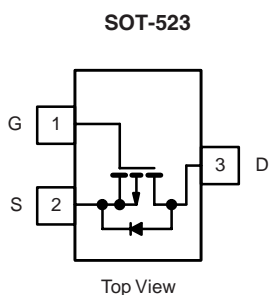
- Halogen-free According to IEC 61249-2-21 Definition
- TrenchFET[®] Power MOSFET
- 100 % R_g Tested
- Compliant to RoHS Directive 2002/95/EC



RoHS
COMPLIANT
HALOGEN
FREE

APPLICATIONS

- Load Switch for Portable Devices
- DC/DC Converter



ABSOLUTE MAXIMUM RATINGS T _A = 25 °C, unless otherwise noted				
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	- 20	V	
Gate-Source Voltage	V _{GS}	± 12		
Continuous Drain Current (T _J = 150 °C)	T _C = 25 °C	- 3.8	A	
	T _C = 70 °C	- 3.0		
	T _A = 25 °C	- 2.8 ^{a, b}		
	T _A = 70 °C	- 2.2 ^{a, b}		
Pulsed Drain Current (10 μs Pulse Width)	I _{DM}	- 15	A	
Continuous Source-Drain Diode Current	T _C = 25 °C	- 1.4		
	T _A = 25 °C	- 0.8 ^{a, b}		
Maximum Power Dissipation	T _C = 25 °C	1.7	W	
	T _C = 70 °C	1.1		
	T _A = 25 °C	0.96 ^{a, b}		
	T _A = 70 °C	0.62 ^{a, b}		
Operating Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to 150	°C	

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Typical	Maximum	Unit	
Maximum Junction-to-Ambient ^{a, c}	R _{thJA}	100	130	°C/W	
Maximum Junction-to-Foot (Drain)	R _{thJF}	60	75		

Notes:

- Surface Mounted on 1" x 1" FR4 board.
- t = 5 s.
- Maximum under Steady State conditions is 175 °C/W.
- T_C = 25 °C.

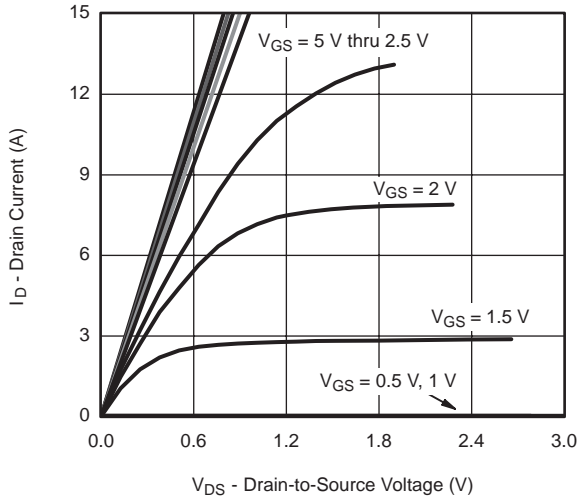
SPECIFICATIONS $T_J = 25\text{ }^\circ\text{C}$, unless otherwise noted						
Parameter	Symbol	Test Conditions	Min.	Typ.	Max.	Unit
Static						
Drain-Source Breakdown Voltage	V_{DS}	$V_{GS} = 0\text{ V}, I_D = -250\text{ }\mu\text{A}$	-20			V
V_{DS} Temperature Coefficient	$\Delta V_{DS}/T_J$	$I_D = -250\text{ }\mu\text{A}$		-20		mV/°C
$V_{GS(th)}$ Temperature Coefficient	$\Delta V_{GS(th)}/T_J$			-2.5		
Gate-Source Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = -250\text{ }\mu\text{A}$	-0.5		-2.5	V
Gate-Source Leakage	I_{GSS}	$V_{DS} = 0\text{ V}, V_{GS} = \pm 8\text{ V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}$			-1	μA
		$V_{DS} = -20\text{ V}, V_{GS} = 0\text{ V}, T_J = 55\text{ }^\circ\text{C}$			-10	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} \leq -5\text{ V}, V_{GS} = -4.5\text{ V}$	-5			A
Drain-Source On-State Resistance ^a	$R_{DS(on)}$	$V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$		0.066	0.072	Ω
		$V_{GS} = -2.5\text{ V}, I_D = -2.0\text{ A}$		0.086	0.092	
		$V_{GS} = -1.8\text{ V}, I_D = -1.5\text{ A}$		0.095	0.105	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -10\text{ V}, I_D = -2.5\text{ A}$		7.5		S
Dynamic^b						
Input Capacitance	C_{iss}	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$		66		pF
Output Capacitance	C_{oss}			112		
Reverse Transfer Capacitance	C_{rss}			89		
Total Gate Charge	Q_g	$V_{DS} = -10\text{ V}, V_{GS} = -8\text{ V}, I_D = -2.5\text{ A}$		15	23	nC
Total Gate Charge	Q_g	$V_{DS} = -10\text{ V}, V_{GS} = -4.5\text{ V}, I_D = -2.5\text{ A}$		9	13.5	
Gate-Source Charge	Q_{gs}			1.0		
Gate-Drain Charge	Q_{gd}			2.5		
Gate Resistance	R_g	$f = 1\text{ MHz}$	2	10	20	Ω
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 5\text{ }\Omega$ $I_D \cong -2\text{ A}, V_{GEN} = -4.5\text{ V}, R_g = 1\text{ }\Omega$		20	40	ns
Rise Time	t_r			20	40	
Turn-Off Delay Time	$t_{d(off)}$			40	70	
Fall Time	t_f			10	20	
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -10\text{ V}, R_L = 5\text{ }\Omega$ $I_D \cong -2\text{ A}, V_{GEN} = -8\text{ V}, R_g = 1\text{ }\Omega$		8	16	
Rise Time	t_r			9	18	
Turn-Off Delay Time	$t_{d(off)}$			35	65	
Fall Time	t_f			9	18	
Drain-Source Body Diode Characteristics						
Continuous Source-Drain Diode Current	I_S	$T_C = 25\text{ }^\circ\text{C}$			-3.8	A
Pulse Diode Forward Current	I_{SM}				-15	
Body Diode Voltage	V_{SD}	$I_S = -2\text{ A}, V_{GS} = 0\text{ V}$		-0.79	-1.2	V
Body Diode Reverse Recovery Time	t_{rr}	$I_F = -2\text{ A}, dI/dt = 100\text{ A}/\mu\text{s}, T_J = 25\text{ }^\circ\text{C}$		21	35	ns
Body Diode Reverse Recovery Charge	Q_{rr}			15	25	nC
Reverse Recovery Fall Time	t_a			9		ns
Reverse Recovery Rise Time	t_b			12		

Notes:

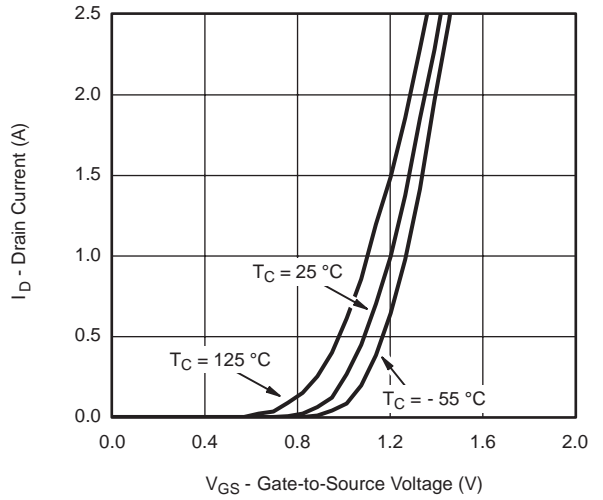
- Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
- Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

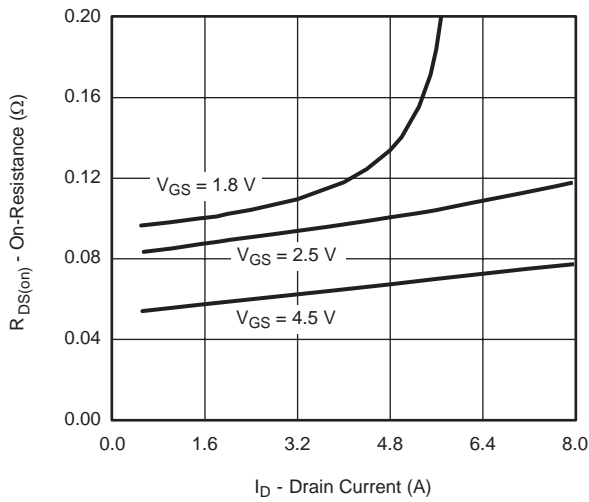
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



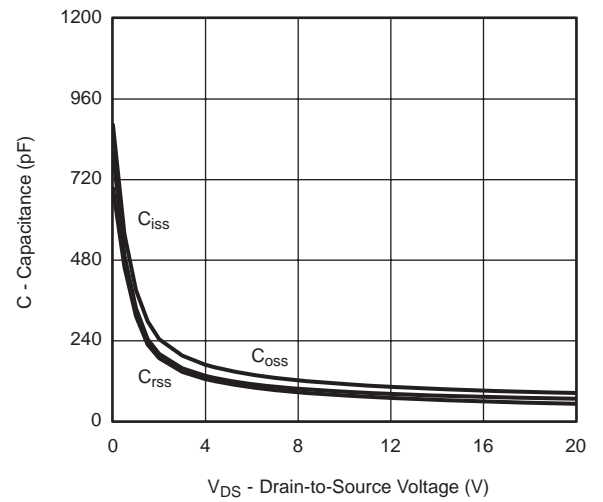
Output Characteristics



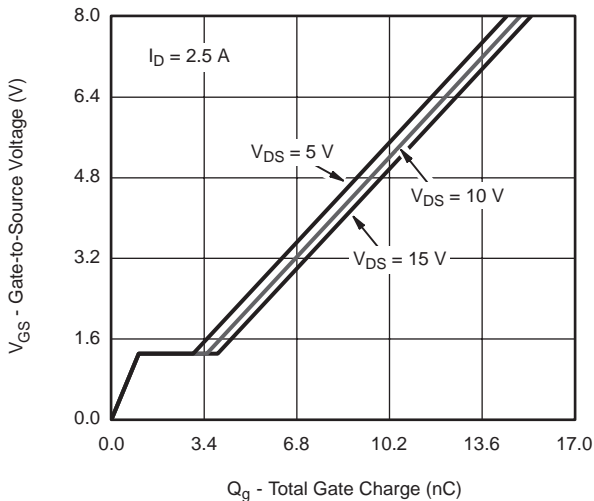
Transfer Characteristics



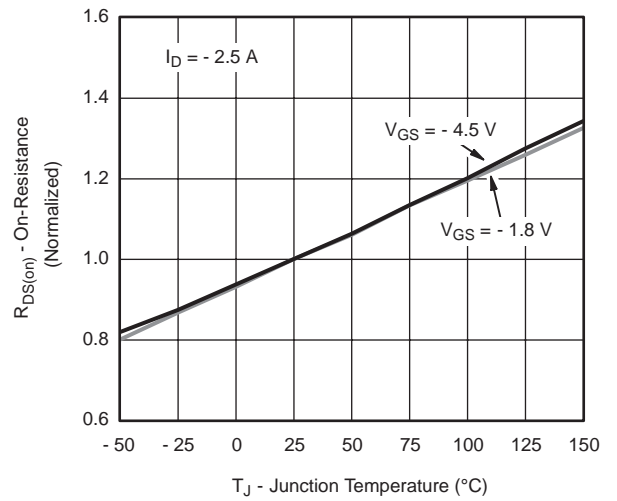
On-Resistance vs. Drain Current and Gate Voltage



Capacitance

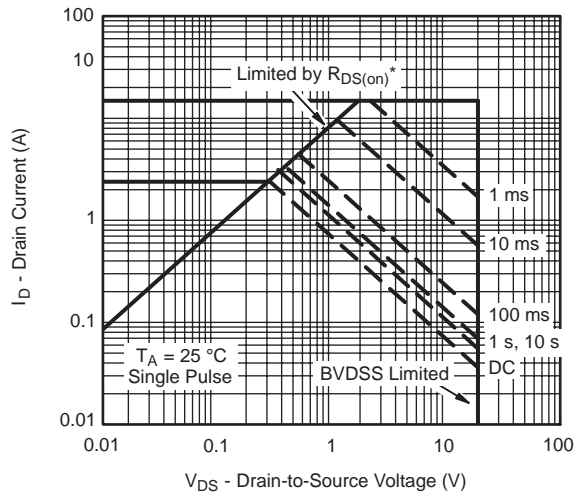
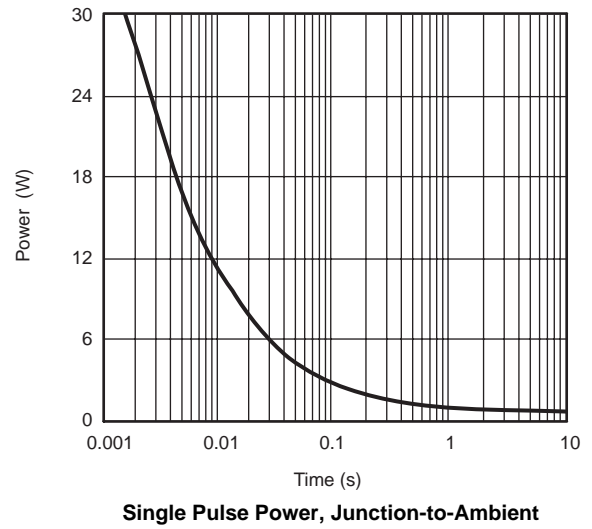
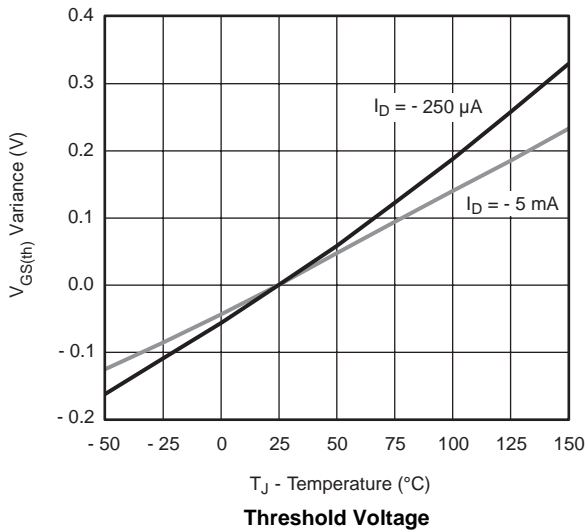
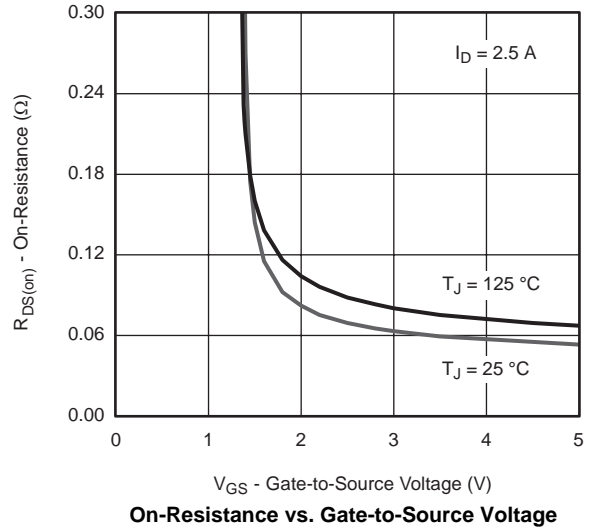
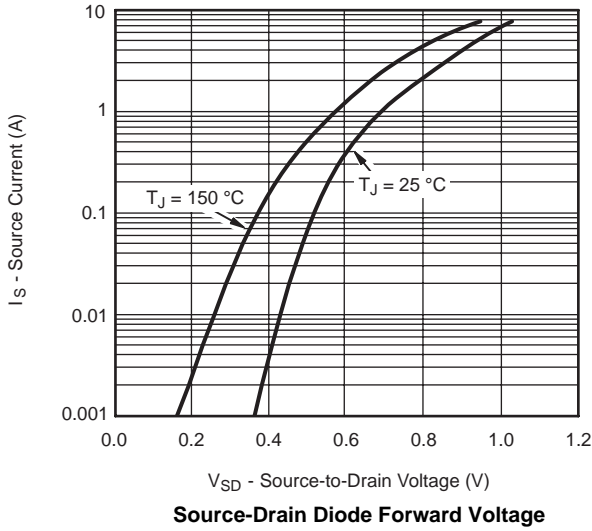


Gate Charge



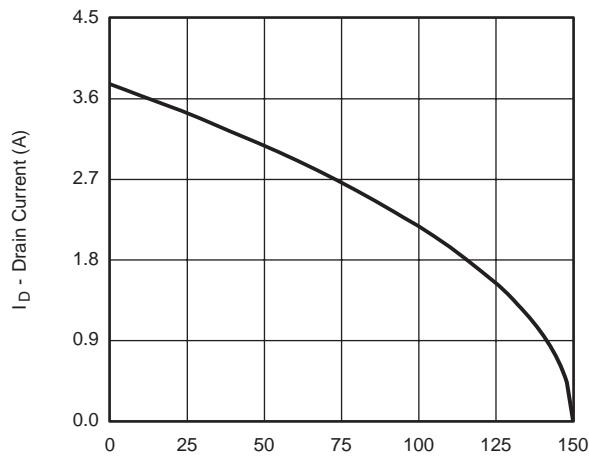
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

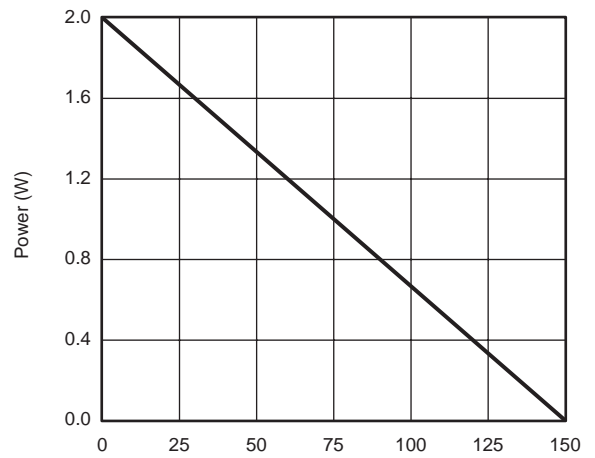


* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

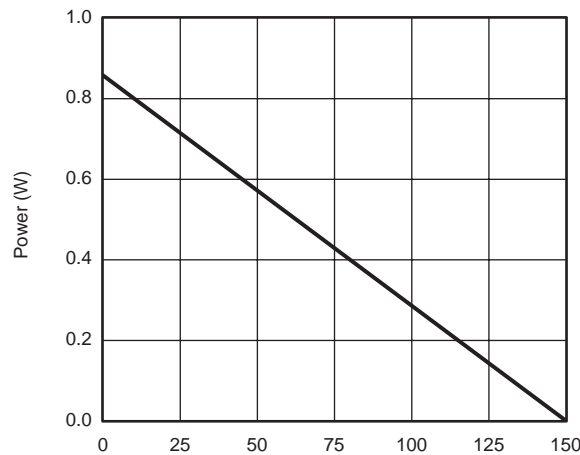
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



T_C - Case Temperature (°C)
Current Derating*



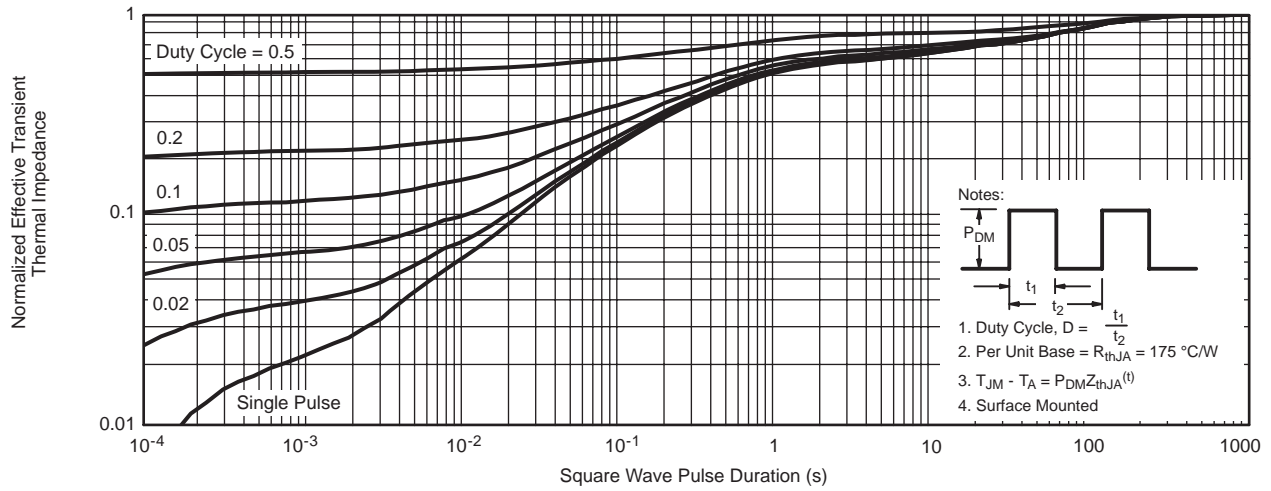
T_C - Case Temperature (°C)
Power Derating, Junction-to-Foot



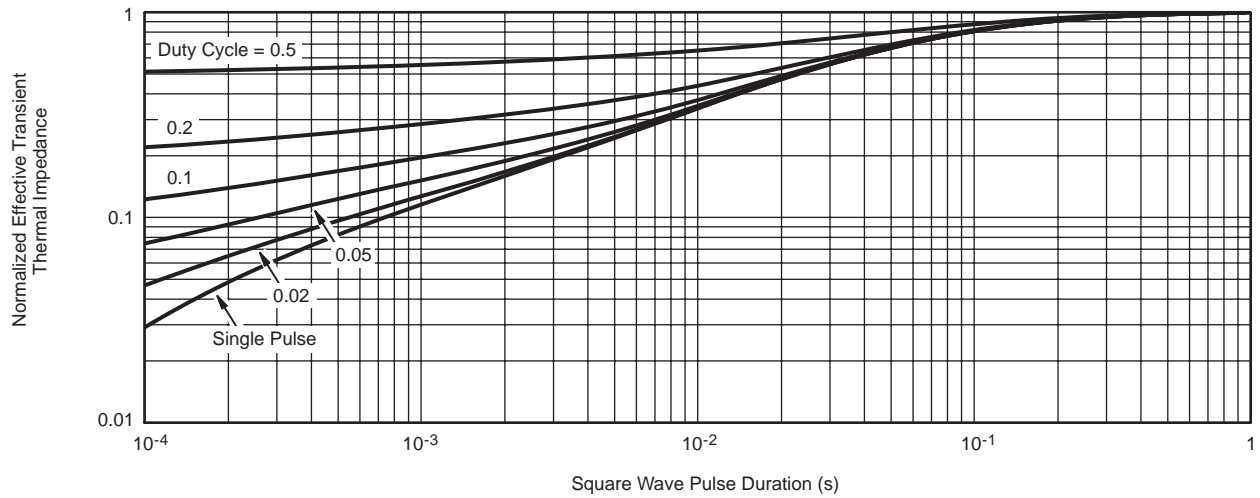
T_A - Ambient Temperature (°C)
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

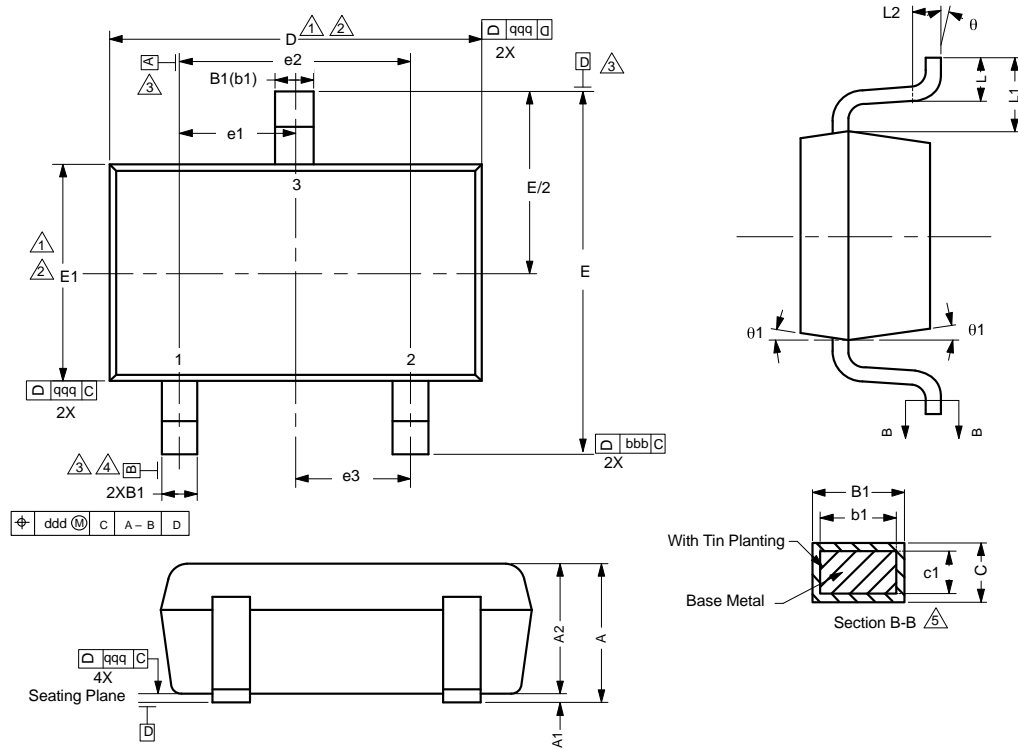


Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Foot

SOT-523: 3 Leads



Notes

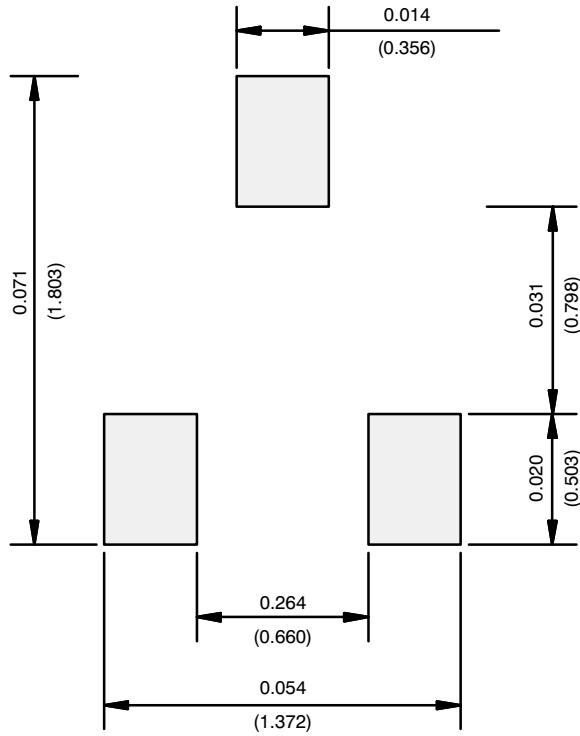
Dimensions in millimeters will govern.

1. Dimension D does not include mold flash, protrusions or gate burrs. Mold flash protrusions or gate burrs shall not exceed 0.10 mm per end. Dimension E1 does not include Interlead flash or protrusion. Interlead flash or protrusion shall not exceed 0.10 mm per side.
2. Dimensions D and E1 are determined at the outmost extremes of the plastic body exclusive of mold flash, tie bar burrs, gate burrs and interlead flash, but including any mismatch between the top and bottom of the plastic body.
3. Datums A, B and D to be determined 0.10 mm from the lead tip.
4. Terminal positions are shown for reference only.
5. These dimensions apply to the flat section of the lead between 0.08 mm and 0.15 mm from the lead tip.

DIMENSIONS	TOLERANCES
aaa	0.10
bbb	0.10
ccc	0.10
ddd	0.10

DIM.	MILLIMETERS			NOTE
	MIN.	NOM.	MAX.	
A	-	-	0.80	
A ₁	0.00	-	0.10	
A ₂	0.65	0.70	0.80	
B ₁	0.19	-	0.24	5
b ₁	0.17	-	0.21	
c	0.13	-	0.15	5
c ₁	0.10	-	0.12	5
D	1.48	1.575	1.68	1, 2
E	1.50	1.60	1.70	
E ₁	0.66	0.76	0.86	1, 2
e ₁	0.50 BSC			
e ₂	1.00 BSC			
e ₃	0.50 BSC			
L	0.15	0.205	0.30	
L ₁	0.40 ref.			
L ₂	0.15 BSC			
θ	0°	-	8°	
θ ₁	4°	-	10°	

RECOMMENDED MINIMUM PADS FOR SOT523: 3-Lead



Recommended Minimum Pads
Dimensions in Inches/(mm)

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